

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Source-Source Voltage			V <sub>SSS</sub>	12	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Source Current (Note 5) V <sub>GS</sub> = 4.5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>S</sub>	24.4 19.6	A
Continuous Source Current (Note 5) V <sub>GS</sub> = 2.5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>S</sub>	16.4 13.1	A
Pulsed Source Current (Note 6)			I <sub>SM</sub>	100	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7)	P <sub>D</sub>	1.10	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 7)	R <sub>θJA</sub>	114.1	°C/W
Power Dissipation (Note 5)	P <sub>D</sub>	2.47	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	R <sub>θJA</sub>	50.7	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Source-Source Breakdown Voltage	BV <sub>SSS</sub>	12	—	—	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1mA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>SSS</sub>	—	—	1	μA	V <sub>SS</sub> = 9.6V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±8V, V <sub>SS</sub> = 0V
		—	—	±1.0	μA	V <sub>GS</sub> = ±5V, V <sub>SS</sub> = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.35	0.8	1.4	V	V <sub>SS</sub> = 10V, I <sub>S</sub> = 1.41mA
Static Source-Source On-Resistance	R <sub>SS(ON)</sub>	1.5	2.27	2.75	mΩ	V <sub>GS</sub> = 4.5V, I <sub>S</sub> = 6A
		1.6	2.36	2.85		V <sub>GS</sub> = 3.8V, I <sub>S</sub> = 6A
		1.7	2.54	3.95		V <sub>GS</sub> = 3.1V, I <sub>S</sub> = 6A
		1.9	2.9	6.1		V <sub>GS</sub> = 2.5V, I <sub>S</sub> = 6A
Diode Forward Voltage	V <sub>SS</sub>	—	0.69	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 6A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C <sub>iss</sub>	—	3062	4593	pF	V <sub>SS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1kHz
Output Capacitance	C <sub>oss</sub>	—	758	1137		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	198	297		
Total Gate Charge	Q <sub>g</sub>	—	45.7	68.6	nC	V <sub>SS</sub> = 8V, V <sub>GS</sub> = 4V, I <sub>S</sub> = 6A
Gate-Source Charge	Q <sub>gs</sub>	—	8.3	12.5		
Gate-Drain Charge	Q <sub>gd</sub>	—	16.0	24.0		
Gate Charge at V <sub>TH</sub>	Q <sub>g(th)</sub>	—	4.5	6.8		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	1005	1508	ns	V <sub>SS</sub> = 8V, V <sub>GS</sub> = 4V, I <sub>S</sub> = 6A
Turn-On Rise Time	t <sub>R</sub>	—	2186	3279		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	2643	3965		
Turn-Off Fall Time	t <sub>F</sub>	—	4193	6290		

- Notes:
- Device mounted on FR-4 material with 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu.
  - Repetitive rating, pulse width limited by junction temperature.
  - Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

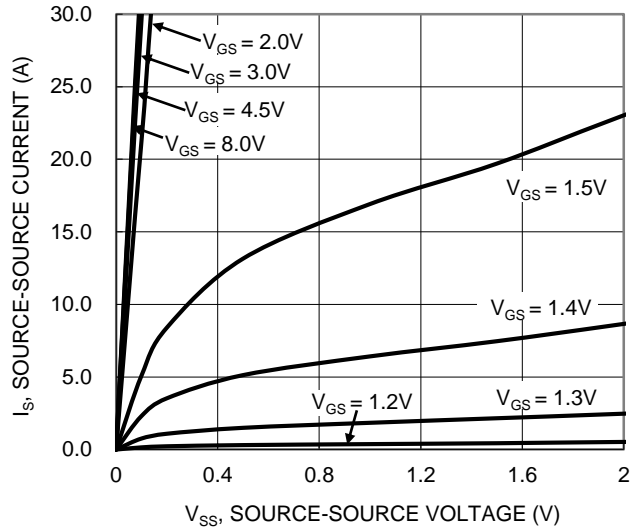


Figure 1. Typical Output Characteristic

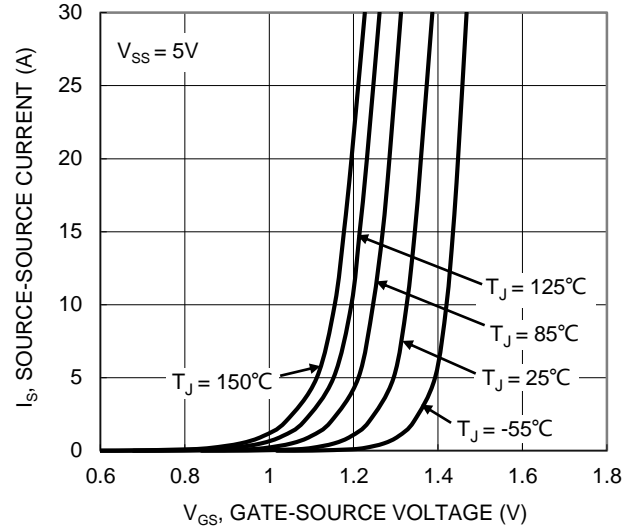


Figure 2. Typical Transfer Characteristic

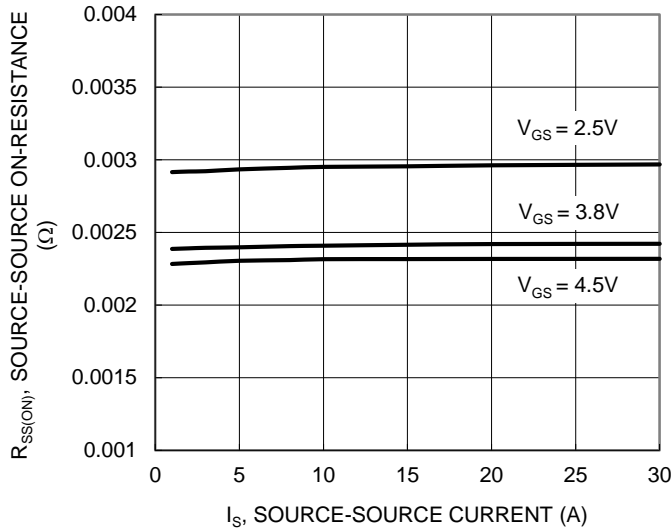


Figure 3. Typical On-Resistance vs. Source Current and Gate Voltage

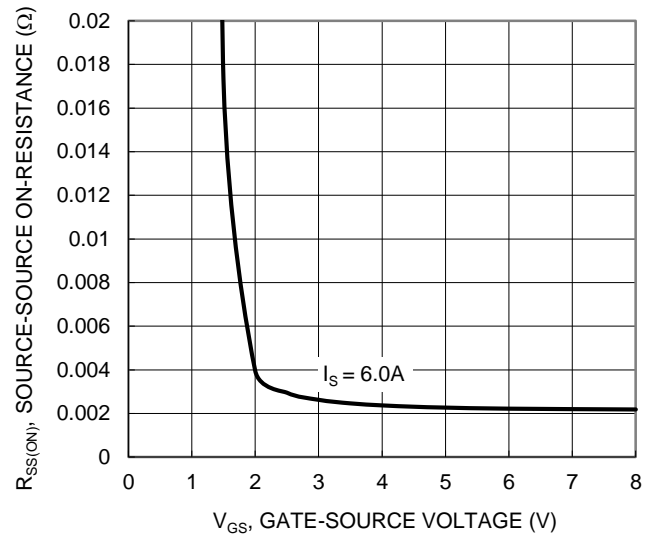


Figure 4. Typical Transfer Characteristic

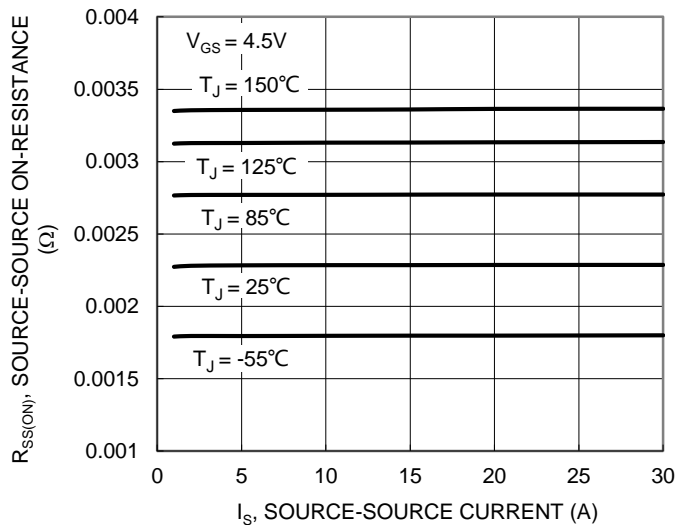


Figure 5. Typical On-Resistance vs. Source Current and Junction Temperature

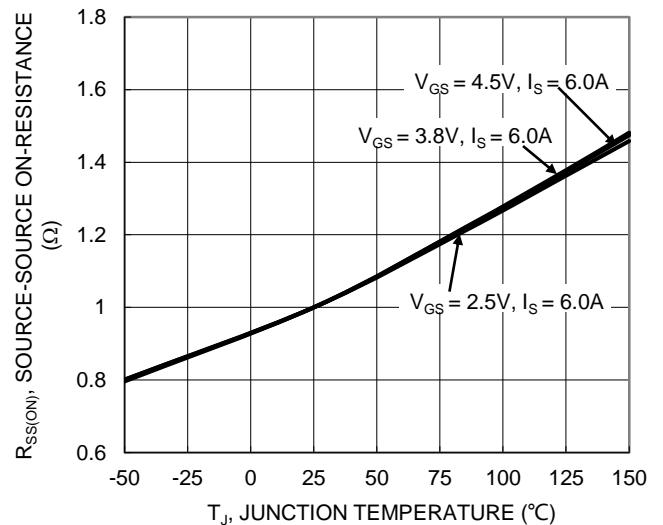


Figure 6. On-Resistance Variation with Junction Temperature

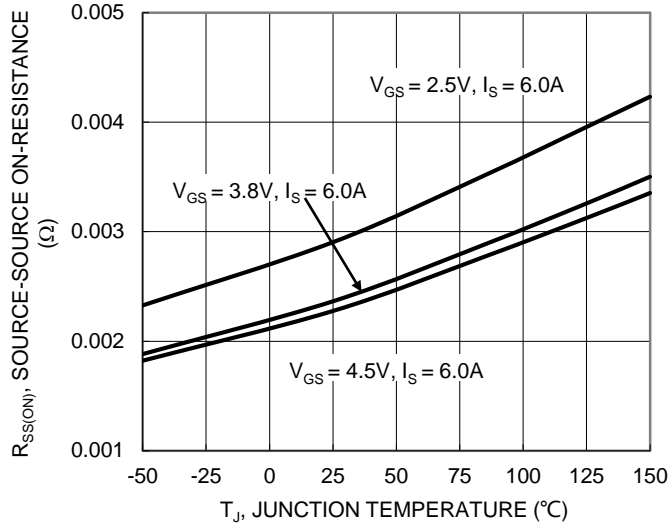


Figure 7. On-Resistance Variation with Junction Temperature

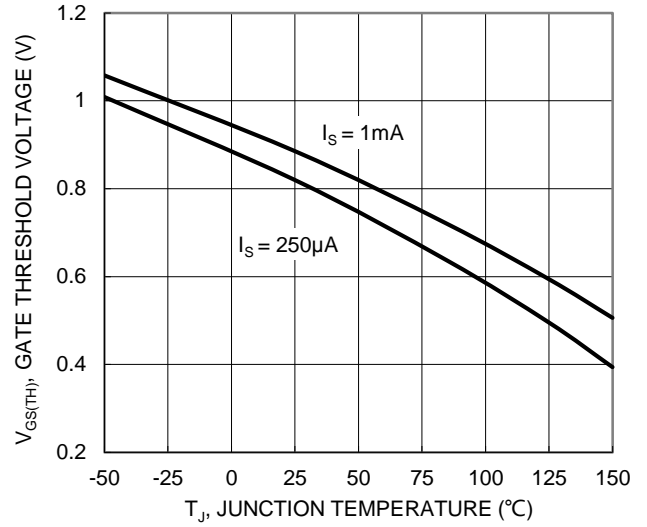


Figure 8. Gate Threshold Variation vs. Junction Temperature

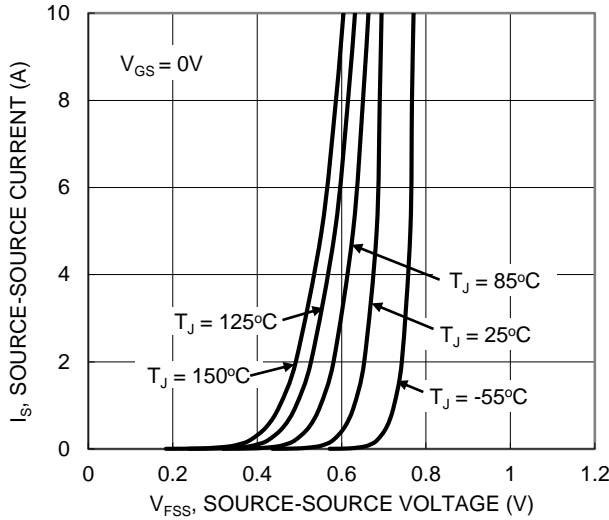


Figure 9. Diode Forward Voltage vs. Current

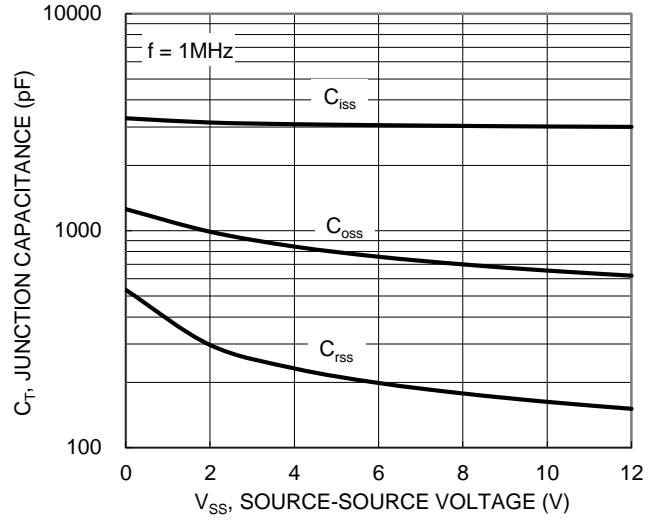


Figure 10. Typical Junction Capacitance

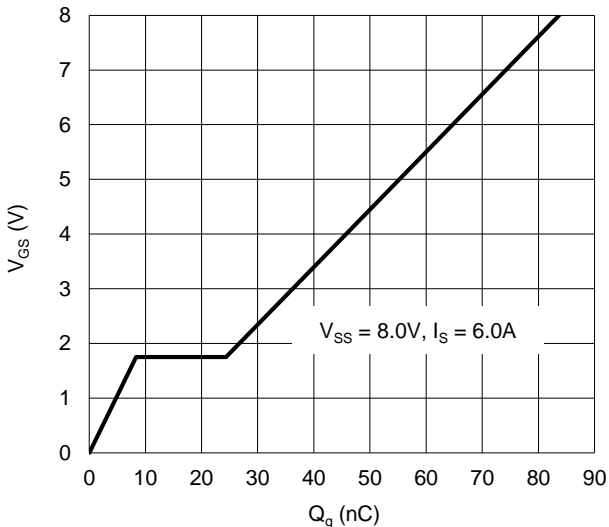


Figure 11. Gate Charge

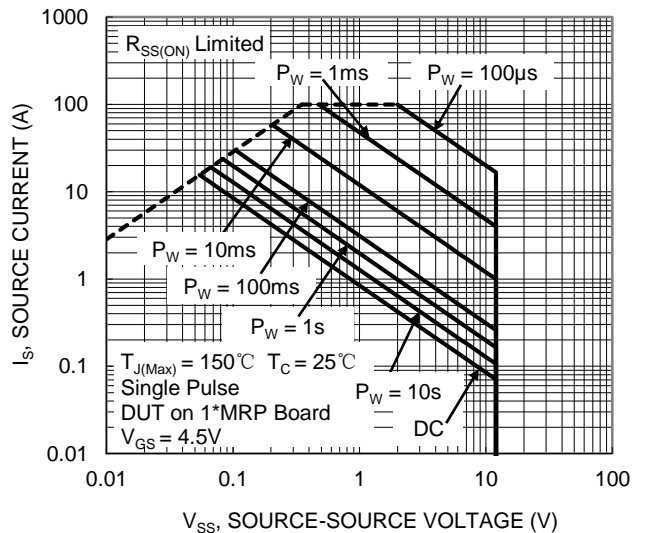


Figure 12. SOA, Safe Operation Area

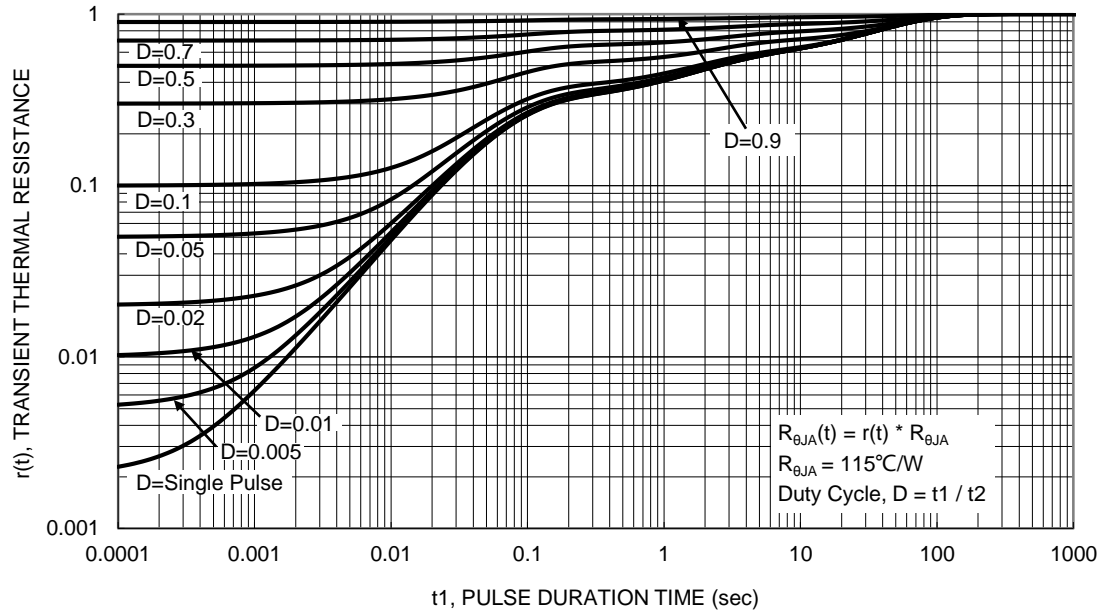
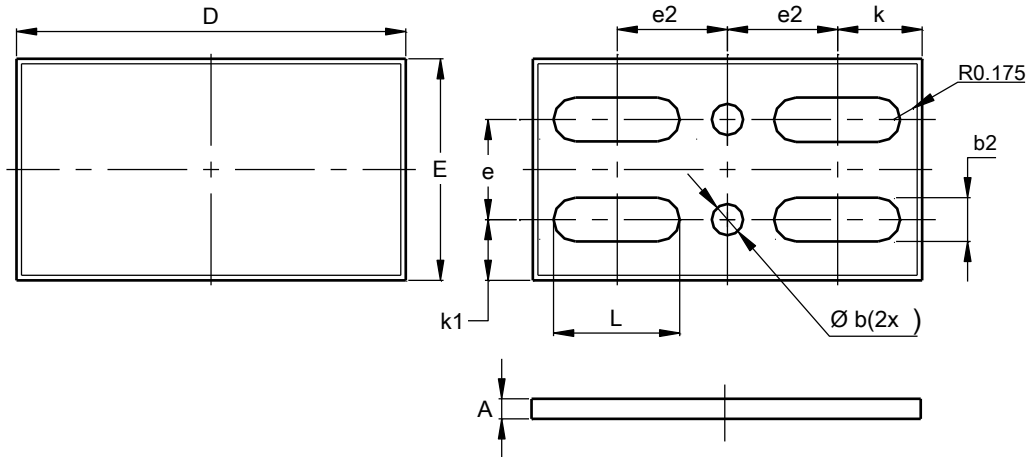


Figure 13. Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X4-DSN3118-6

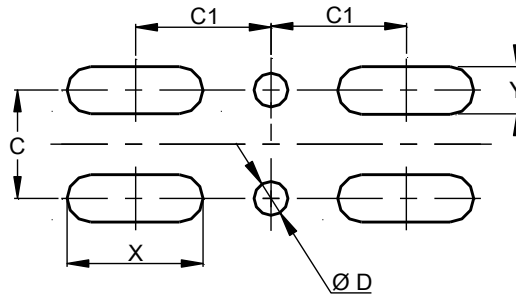


X4-DSN3118-6			
Dim	Min	Max	Typ
A	0.09	0.16	0.11
b	--	--	0.25
b2	0.32	0.38	0.35
D	3.00	3.10	3.05
E	1.72	1.82	1.77
e	--	--	0.800
e2	--	--	0.878
k	--	--	0.648
k1	--	--	0.485
L	0.975	1.035	1.005
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X4-DSN3118-6



Dimensions	Value (in mm)
C	0.800
C1	0.878
D	0.250
X	1.005
Y	0.350

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